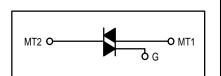
# Silicon Bidirectional Triode Thyristors

... designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Isolated Construction for Low Thermal Resistance, High Heat Dissipation and Durability



ISOLATED TRIACs THYRISTORS

**6 AMPERES RMS** 

200 thru 800 VOLTS

**T2500FP** 

**Series** 

CASE 221C-02 STYLE 3

## **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted.)

Rating	Symbol	Value	Unit
Repetitive Peak Off-State Voltage <sup>(1)</sup> ( $T_J = -40$ to +100°C, Gate Open)	VDRM		Volts
T2500BFP T2500DFP T2500MFP T2500NFP		200 400 600 800	
On-State RMS Current ( $T_C = +80^{\circ}C$ )(2) (Full Cycle Sine Wave 50 to 60 Hz)	<sup>I</sup> T(RMS)	6	Amps
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, T <sub>C</sub> = +80°C)	ITSM	60	Amps
Circuit Fusing Considerations (t = 8.3 ms)	l <sup>2</sup> t	40	A <sup>2</sup> s
Peak Gate Power (T <sub>C</sub> = +80°C, Pulse Width = 1 $\mu$ s)	PGM	1	Watt
Average Gate Power ( $T_C = +80^{\circ}C$ , t = 8.3 ms)	PG(AV)	0.2	Watt
Peak Gate Trigger Current (Pulse Width = 10 μs)	IGTM	4	Amps
RMS Isolation Voltage (T <sub>A</sub> = 25°C, Relative Humidity $\leq$ 20%)	VISO	1500	Volts
Operating Junction Temperature Range	ТJ	-40 to +100	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case <sup>(2)</sup>	R <sub>θ</sub> JC	2.7	°C/W
Case to Sink	R <sub>θ</sub> CS	2.2(typ)	
Junction to Ambient	R <sub>θ</sub> JA	60	

1. V<sub>DRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

2. The case temperature reference point for all T<sub>C</sub> measurements is a point on the center lead of the package as close as possible to the plastic body.



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ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Off-State Current (Either Direction) $(V_D = Rated V_{DRM}, T_J = 100^{\circ}C, Gate Open)$	IDRM	-	—	2	mA
Maximum On-State Voltage (Either Direction)* (I <sub>T</sub> = 30 A Peak)	VTM	-	-	2	Volts
Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ Vdc}, \text{ R}_L = 12 \text{ Ohms})$ MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	lgt	 	10 20 15 30	25 60 25 60	mA
Gate Trigger Voltage (Continuous dc) (All Quadrants) ( $V_D = 12 \text{ Vdc}, \text{ R}_L = 12 \text{ Ohms}$ ) ( $V_D = V_{DROM}, \text{ R}_L = 125 \text{ Ohms}, \text{ T}_C = 100^{\circ}\text{C}$ , All Trigger Models)	VGT		1.25 —	2.5 —	Volts
Holding Current (Either Direction) (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = 150 mA, $T_C = 25^{\circ}C$ )	Ч	-	15	30	mA
Gate Controlled Turn-On Time (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>T</sub> = 10 A, I <sub>GT</sub> = 160 mA, Rise Time $\leq 0.1 \ \mu$ s)	<sup>t</sup> gt	-	1.6	_	μs
Critical Rate-of-Rise of Commutation Voltage $(V_D = Rated V_{DRM}, I_T(RMS) = 6 A,$ Commutating di/dt = 3.2 A/ms, Gate Unenergized, T <sub>C</sub> = 80°C)	dv/dt(c)	_	10	_	V/µs
Critical Rate-of-Rise of Off-State Voltage ( $V_D$ = Rated $V_{DRM}$ , Exponential Voltage Rise, Gate Open, T <sub>C</sub> = 100°C)	dv/dt	-	100	_	V/µs

\*Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2%.

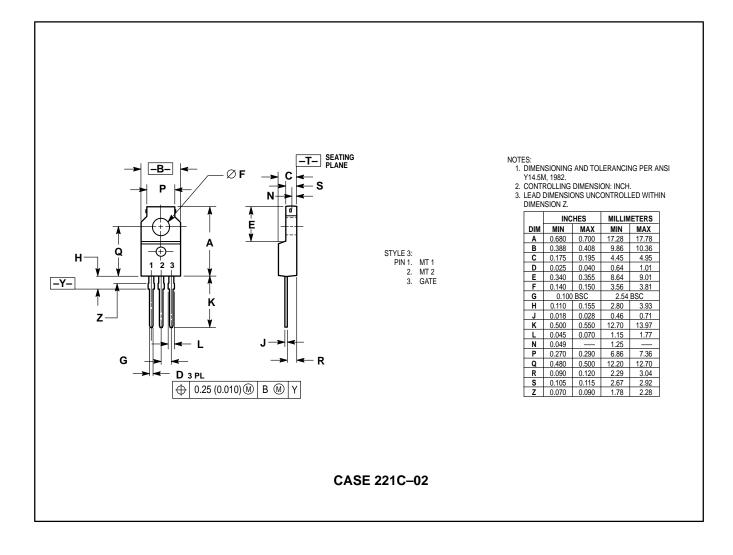
### **Quadrant Definitions**

MT2(+)		
Quadrant II	Quadrant I	
MT2(+), G(-)	MT2(+), G(+)	
G(-)	G(+)	
Quadrant III	Quadrant IV	
MT2(-), G(-)	MT2(-), G(+)	
MT2(-)		

- Trigger devices are recommended for gating on Triacs. They provide:
  1. Consistent predictable turn-on points.
  2. Simplified circuitry.
  3. Fast turn-on time for cooler, more efficient and reliable operation.

#### **Electrical Characteristics of Recommended Bidirectional Switches**

Usage	General		
Part Number	MBS4991	MBS4992	
٧ <sub>S</sub>	6 – 10 V	7.5 – 9 V	
IS	350 μA Max	120 µA Max	
V <sub>S1</sub> - V <sub>S2</sub>	0.5 V Max	0.2 V Max	
Temperature Coefficient	0.02%/°C Тур		



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